Electronic Supplementary Information

Investigation of the *I-V* characteristics of n^+/n homojunctions introduced by heavy ion irradiation in CdZnTe crystals

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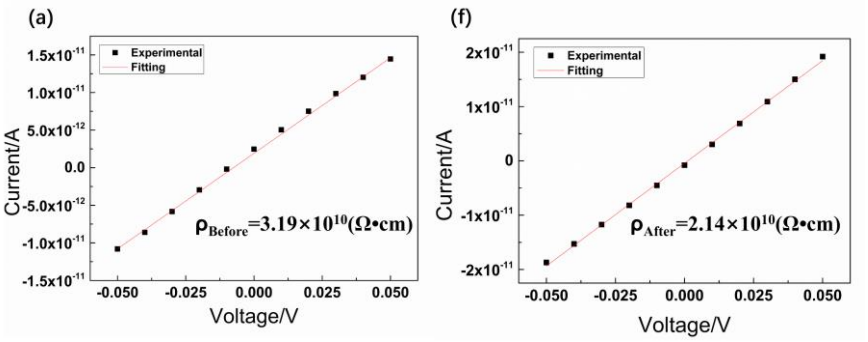
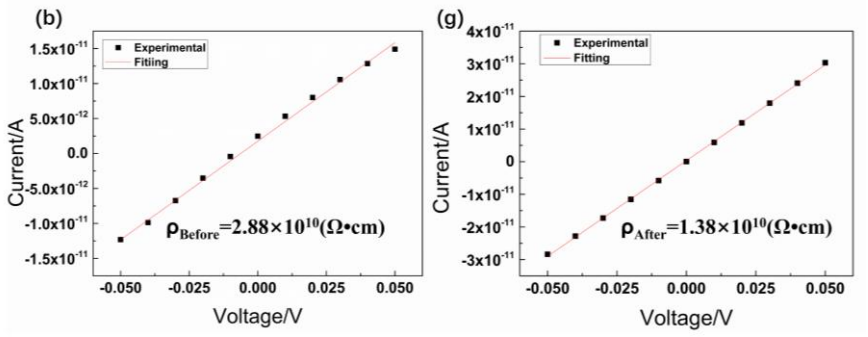
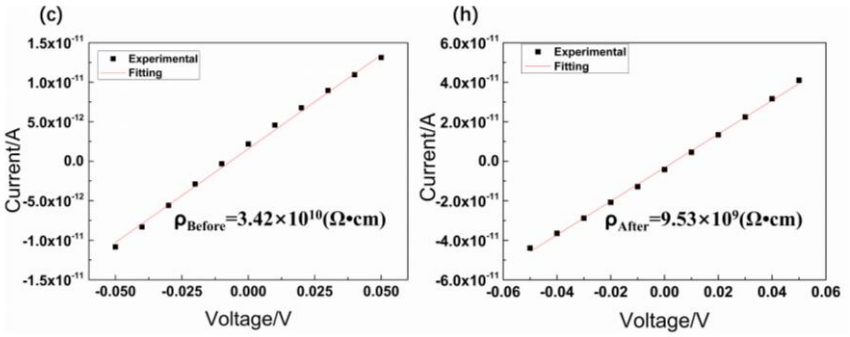
irradiation fluence: 1×10^{11} n/cm^2



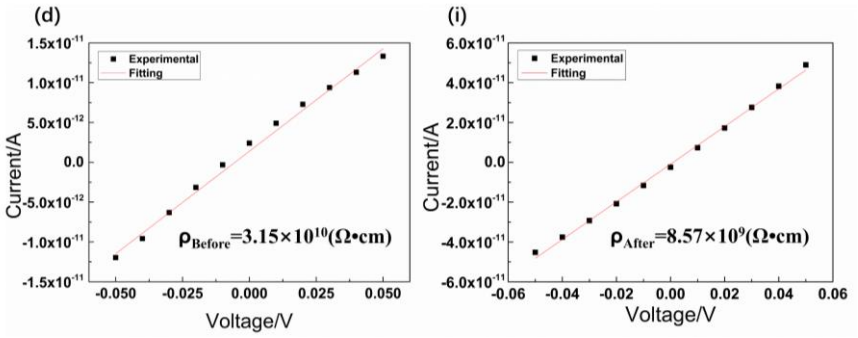
irradiation fluence: 5×10^{11} n/cm^2



irradiation fluence: 2.5×10^{12} n/cm^2



irradiation fluence: 1×10^{13} n/cm^2



irradiation fluence: 1.4×10^{13} n/cm^2

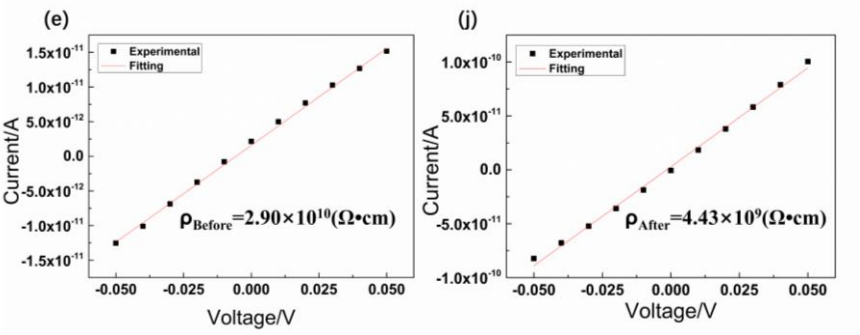


Figure S1. The electric resistivity of five CdZnTe crystals before (a~e) and after (f~j) irradiation

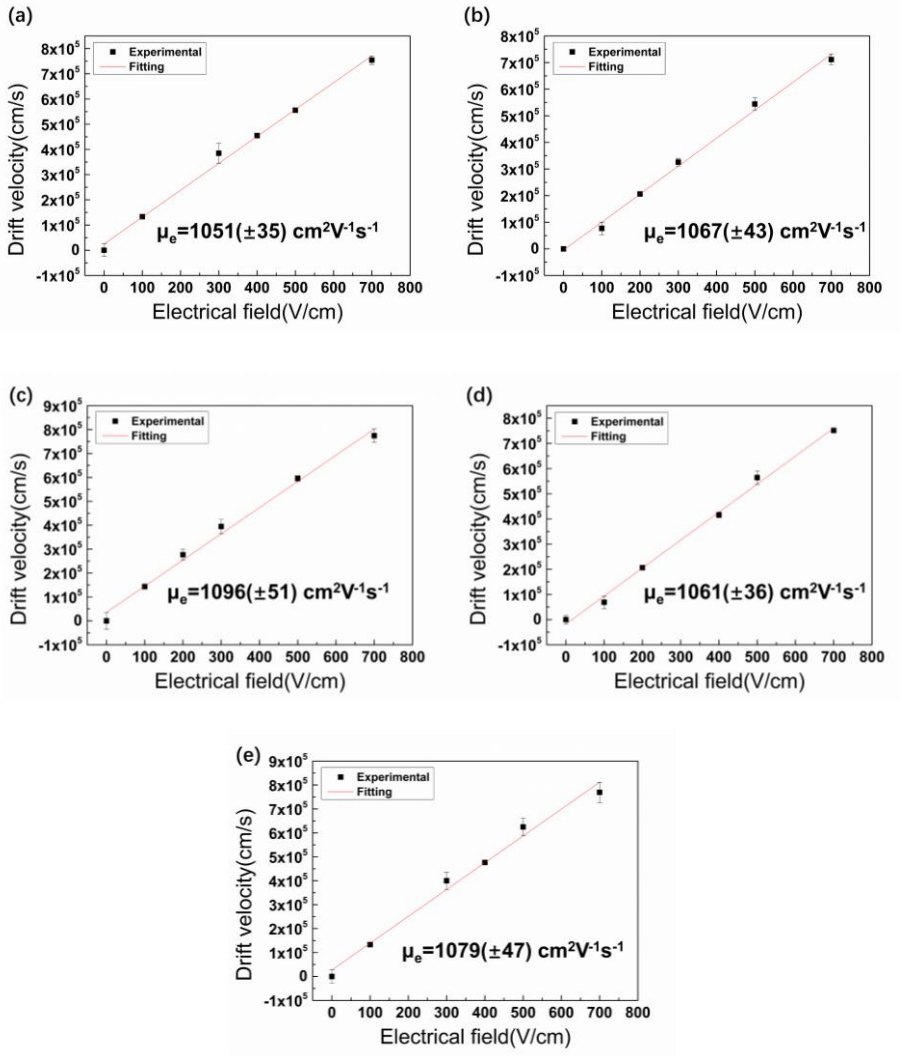


Figure S2. The electron mobility of five CdZnTe crystals before irradiation